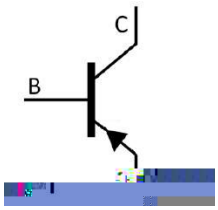
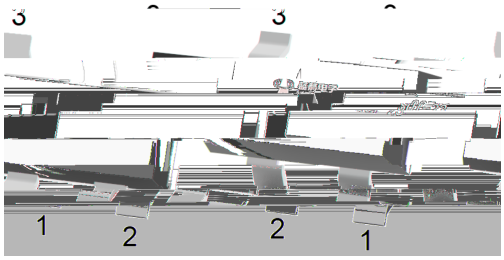
SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

PC IC ,hFE , 9013M

High P_C and I_C, Excellent h_{FE} linearity, complementary pair with 9013M,HF Product.

Amplifier of portable radios in class B push-pull operation.





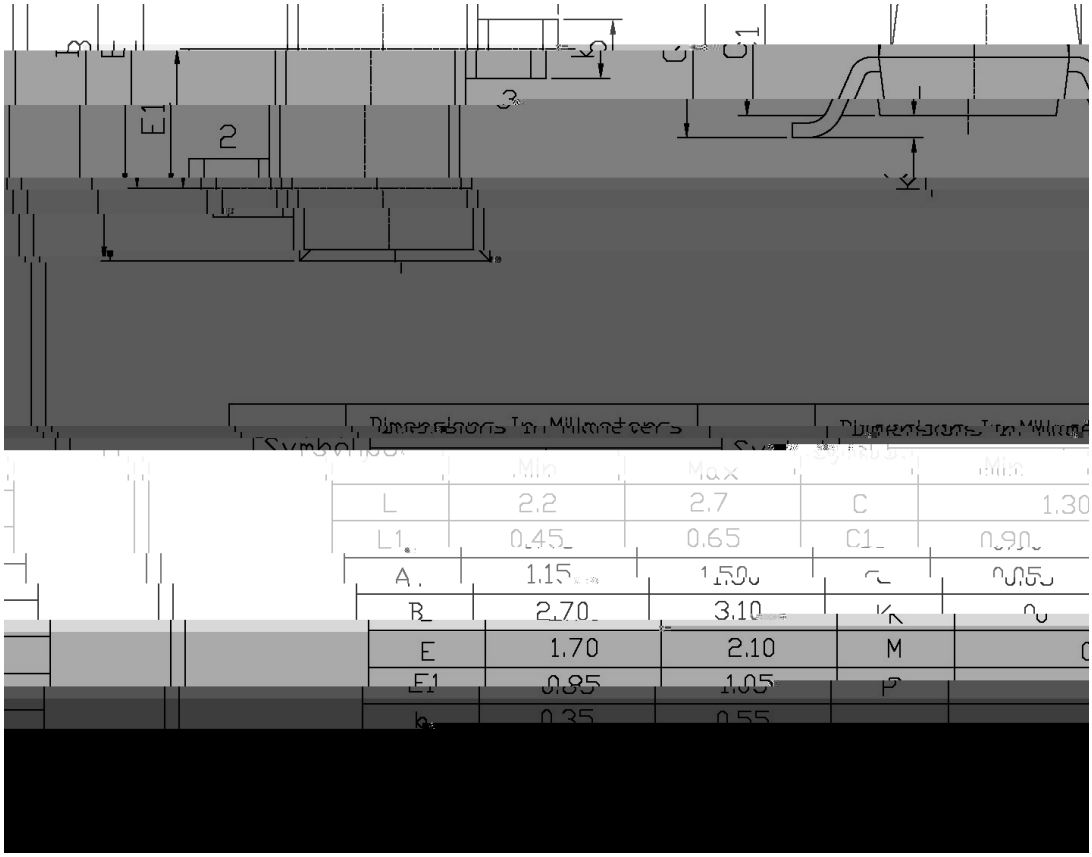
PIN1 Base PIN 2 Emitter PIN 3 Collector

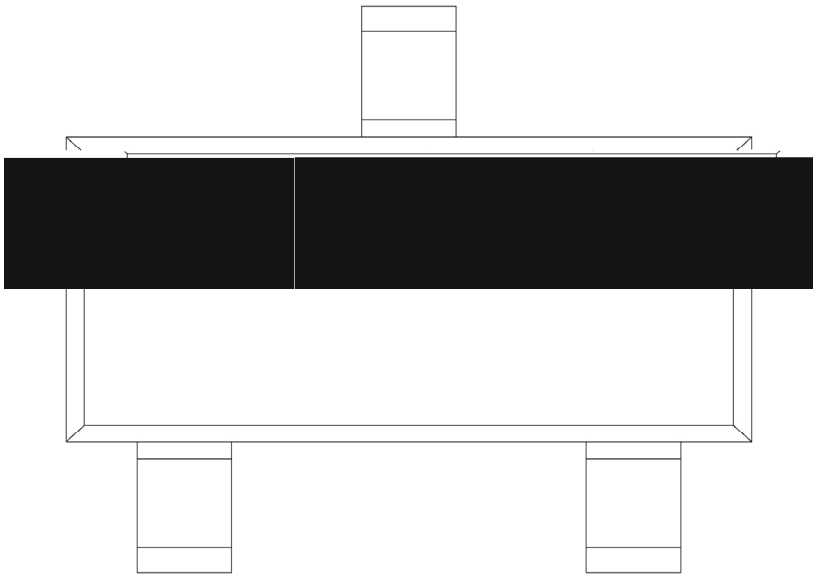
h_{FE} Classifications Symbol	D	E	F	G	H	I
h_{FE} Range	64 91	78 112	96 135	112 166	144 202	188 276
Marking	H2TD	H2TE	H2TF	H2TG	H2TH	H2TI

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-500	mA
Base Current	I_B	-100	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-0.1mA I_E=0	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-20			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-0.1mA I_C=0	-5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-25V I_E=0			-0.1	

484.08


E1
2
3
C
C1
Dimensions In Millimeters
Dimensions In Millimeters
Symbol
Min
Max
Symbol
Min
L
2.2
2.7
C
1.30
L1
0.45
0.65
C1
0.90
A
1.15
1.50
0.05
B
2.70
3.10
E
1.70
2.10
M
E1
0.85
1.05
b
0.35
0.55



H

2T

D h_{FE}

Note:

H	Company Code
2T	Product Type Code
D	h_{FE} Classifications Symbol Code

Temperature Profile for IR Reflow Soldering(Pb-Free)



		Note:
1	150 180 60 90sec;	1.Preheating:150~180 , Time:60~90sec.
2	245±5 5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3	2 10 /sec.	3. Cooling Speed: 2~10 /sec.

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ REEL

Package Type	Units	Dimension	(unit mm³)